

NPN DARLINGTON POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/502

Devices

2N6058

2N6059

Qualified Level

JANTX
JANTXV

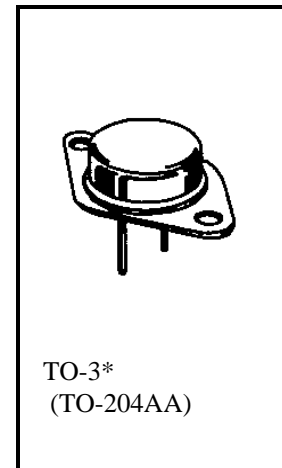
MAXIMUM RATINGS

Ratings	Symbol	2N6058	2N6059	Units
Collector-Emitter Voltage	V_{CEO}	80	100	Vdc
Collector-Base Voltage	V_{CBO}	80	100	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Base Current	I_B	0.2		Adc
Collector Current	I_C	12		Adc
Total Power Dissipation ⁽¹⁾	P_T	@ $T_C = +25^{\circ}C$	150	W
		@ $T_C = +100^{\circ}C$	75	W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-55 to +175		$^{\circ}C$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.0	$^{\circ}C/W$

1) Derate linearly at 1.0 W/ $^{\circ}C$ above $T_C > +25^{\circ}C$



*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
-----------------	--------	------	------	------

OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 100 \text{ mAdc}$	2N6058 2N6059	$V_{(BR)CEO}$	80 100	Vdc
Collector-Emitter Cutoff Current $V_{CE} = 40 \text{ Vdc}$ $V_{CE} = 50 \text{ Vdc}$	2N6058 2N6059	I_{CEO}	1.0 1.0	mAdc
Collector-Emitter Cutoff Current $V_{CE} = 80 \text{ Vdc}, V_{BE} = 1.5 \text{ Vdc}$ $V_{CE} = 100 \text{ Vdc}, V_{BE} = 1.5 \text{ Vdc}$	2N6058 2N6059	I_{CEX}	0.5 0.5	mAdc
Emitter-Base Cutoff Current $V_{EB} = 5.0 \text{ Vdc}$		I_{EBO}	2.0	mAdc

